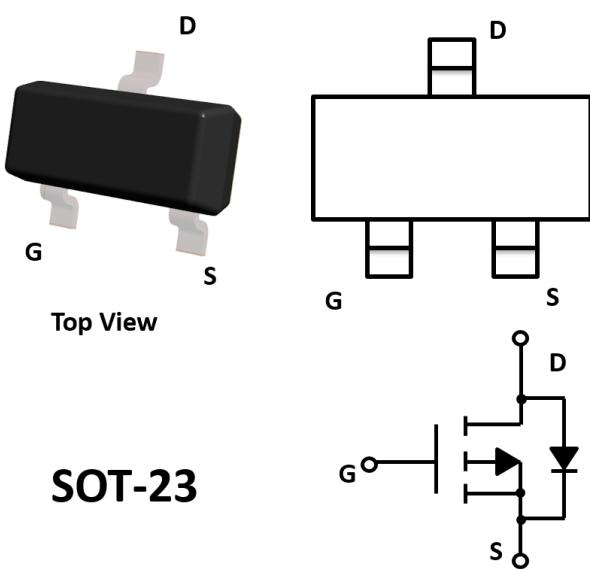


## P-Channel Enhancement Mode Field Effect Transistor



### ■ Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Maximum	Unit
Drain-source Voltage	$V_{DS}$	-12	V
Gate-source Voltage	$V_{GS}$	$\pm 8$	V
Drain Current	$I_D$	-6	A
Pulsed Drain Current <sup>A</sup>	$I_{DM}$	-20	A
Total Power Dissipation @ $T_A=25^\circ\text{C}$ Steady State	$P_D$	1.2	W
Thermal Resistance Junction-to-Ambient @ Steady State <sup>B</sup>	$R_{\theta JA}$	104	$^\circ\text{C} / \text{W}$
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~+150	$^\circ\text{C}$

■ Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-12			V
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{\text{DS}}=-12\text{V}, V_{\text{GS}}=0\text{V}, T_c=25^\circ\text{C}$			-1	$\mu\text{A}$
Gate-Body Leakage Current	$I_{\text{GSS}}$	$V_{\text{GS}}= \pm 8\text{V}, V_{\text{DS}}=0\text{V}$			$\pm 100$	nA
Gate Threshold Voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}= V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$	-0.4	-0.6	-1.0	V
Static Drain-Source On-Resistance	$R_{\text{DS(ON)}}$	$V_{\text{GS}}= -4.5\text{V}, I_{\text{D}}=-5.4\text{A}$		30	40	$\text{m}\Omega$
		$V_{\text{GS}}= -2.5\text{V}, I_{\text{D}}=-4.0\text{A}$		37	50	
		$V_{\text{GS}}= -1.8\text{V}, I_{\text{D}}=-1.0\text{A}$		58	70	
Diode Forward Voltage	$V_{\text{SD}}$	$I_{\text{S}}=-4\text{A}, V_{\text{GS}}=0\text{V}$		-0.8	-1.2	V
Maximum Body-Diode Continuous Current	$I_{\text{S}}$				-6	A
<b>Dynamic Parameters</b>						
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}}=-4\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$		740		$\text{pF}$
Output Capacitance	$C_{\text{oss}}$			290		
Reverse Transfer Capacitance	$C_{\text{rss}}$			190		
<b>Switching Parameters</b>						
Total Gate Charge	$Q_{\text{g}}$	$V_{\text{GS}}=-2.5\text{V}, V_{\text{DS}}=-4\text{V}, I_{\text{D}}=-4\text{A}$		4.5		$\text{nC}$
Gate Source Charge	$Q_{\text{gs}}$			1.2		
Gate Drain Charge	$Q_{\text{gd}}$			1.6		
Turn-on Delay Time	$t_{\text{D(on)}}$	$V_{\text{GEN}}=-8\text{V}, V_{\text{DD}}=-4\text{V}, R_{\text{L}}=1.2\Omega, I_{\text{D}}=-3.3\text{A}$		5		$\text{ns}$
Turn-on Rise Time	$t_{\text{r}}$			11		
Turn-off Delay Time	$t_{\text{D(off)}}$			22		
Turn-off Fall Time	$t_{\text{f}}$			16		

A. Pulse Test: Pulse Width  $\leq 300\text{us}$ , Duty cycle  $\leq 2\%$ .

B. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.

## ■ Typical Performance Characteristics

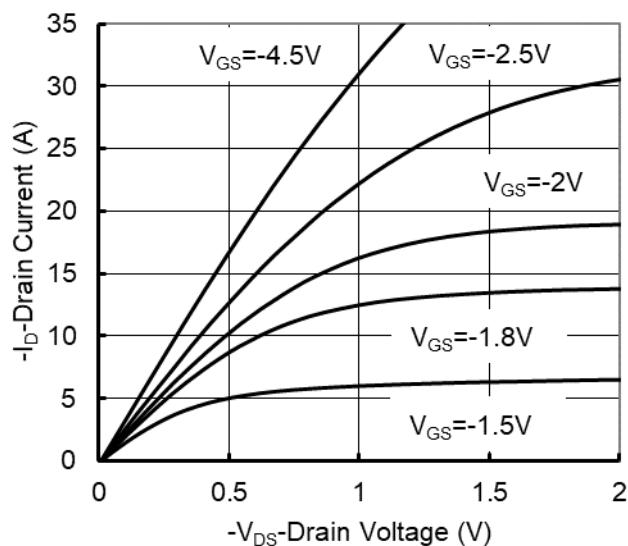


Figure 1. Output Characteristics

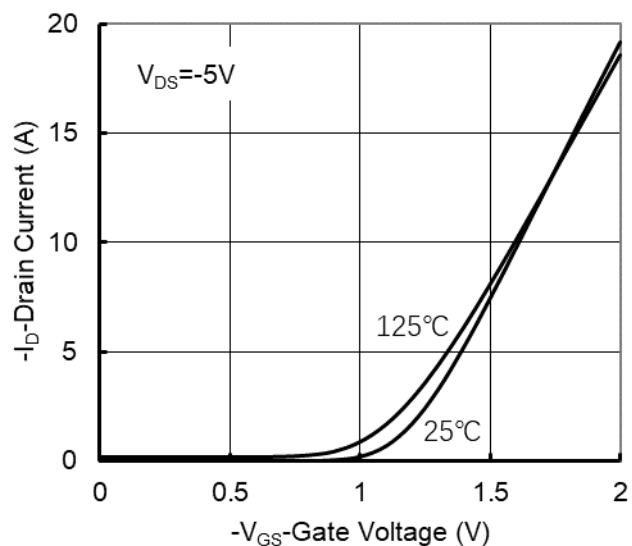


Figure 2. Transfer Characteristics

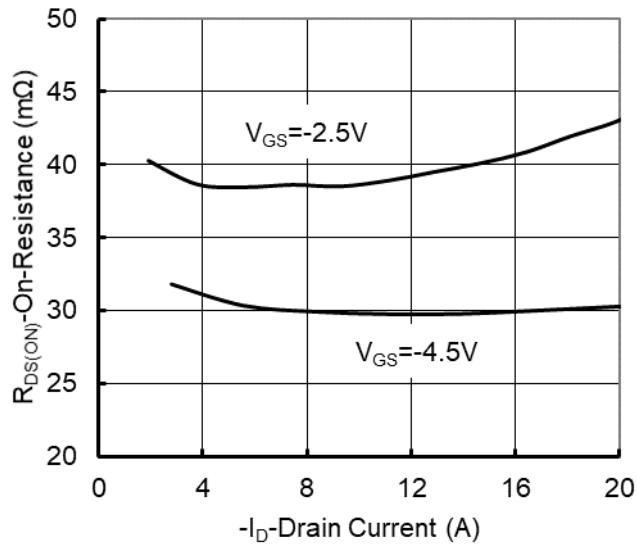


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

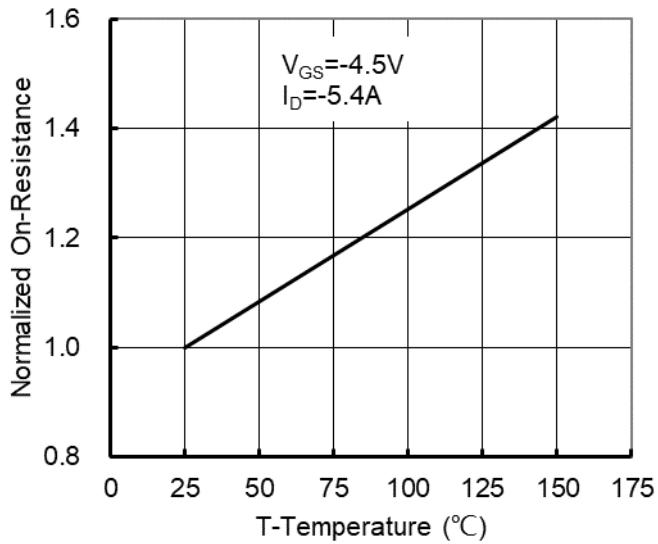


Figure 4: On-Resistance vs. Junction Temperature

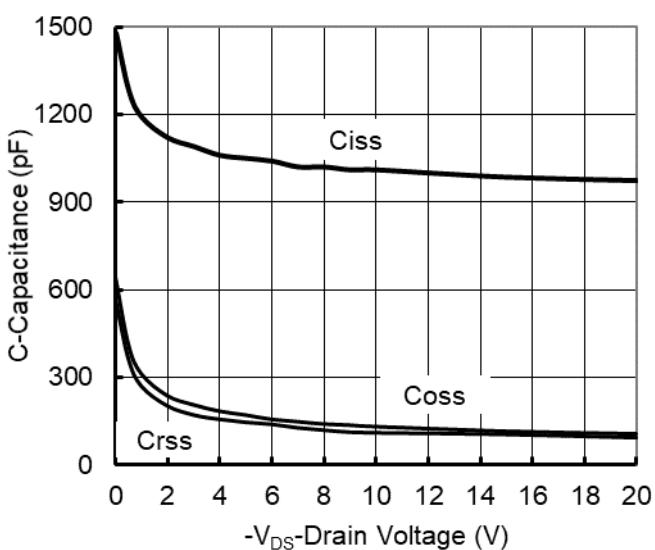


Figure 5. Capacitance Characteristics

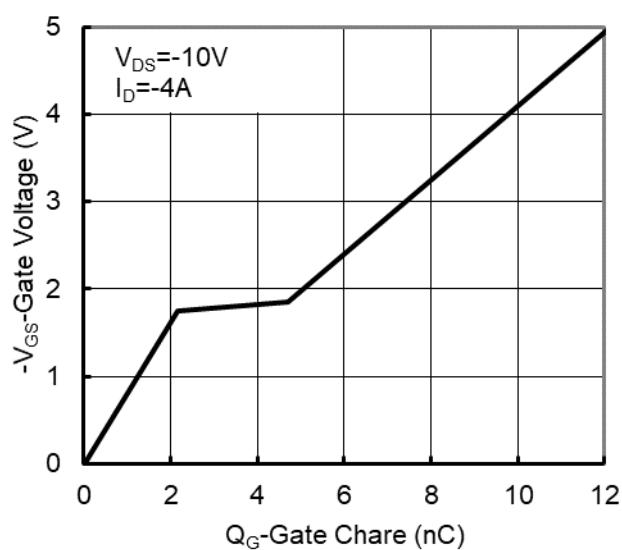


Figure 6. Gate Charge

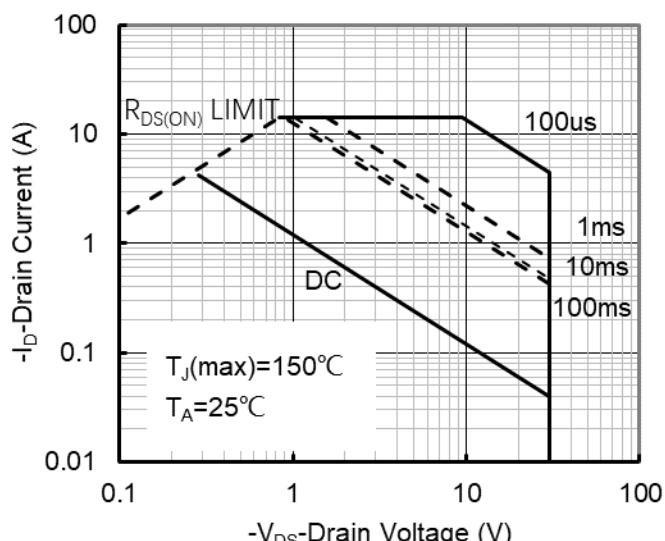


Figure7. Safe Operation Area

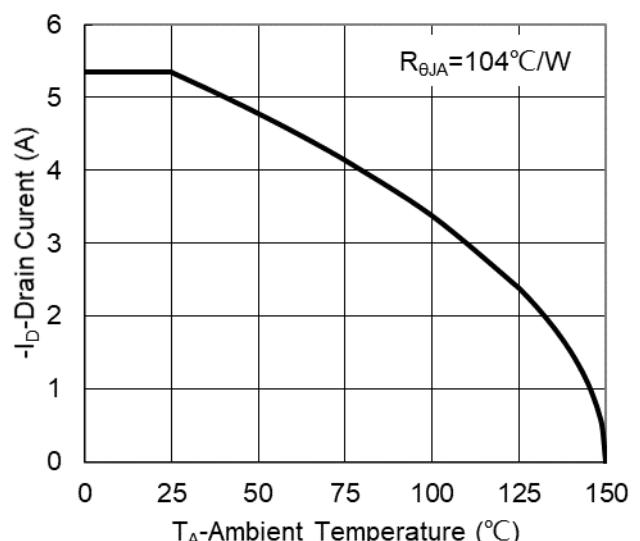
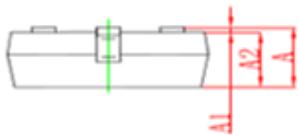
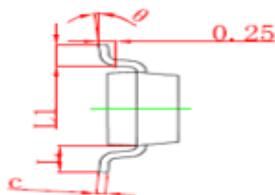
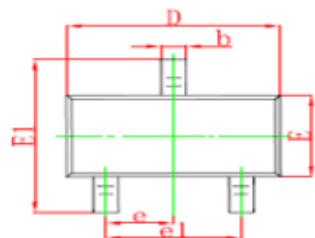
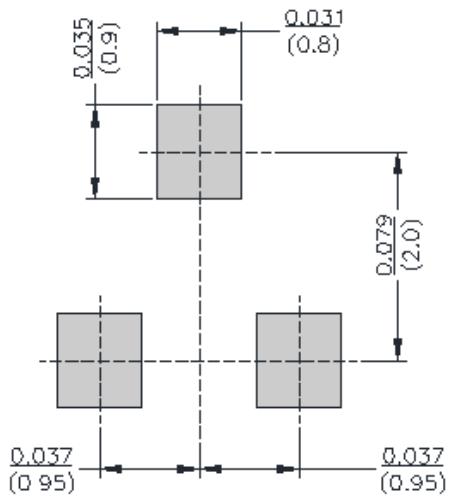


Figure8. Maximum Continuous Drain Current  
vs Ambient Temperature

**■ SOT-23 Package information**

Symbol	Dimensions in Millimeter		Dimensions in Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950Type		0.037Type	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.220REF	
L1	0.300	0.500	0.012	0.020
θ	0 °	8 °	0 °	8 °

**■ SOT-23 Suggested Pad Layout**

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